



SN65HVD20, SN65HVD21 SN65HVD22, SN65HVD23, SN65HVD24

SLLS552E - DECEMBER 2002 - REVISED MAY 2010

Extended Common-Mode RS-485 Transceivers

Check for Samples: SN65HVD20, SN65HVD21, SN65HVD22, SN65HVD23, SN65HVD24

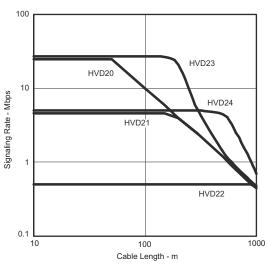
FEATURES

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- Common-Mode Voltage Range (–20 V to 25 V) More Than Doubles TIA/EIA-485 Requirement
- Receiver Equalization Extends Cable Length, Signaling Rate (HVD23, HVD24)
- Reduced Unit-Load for up to 256 Nodes
- Bus I/O Protection to Over 16-kV HBM
- Failsafe Receiver for Open-Circuit, Short-Circuit and Idle-Bus Conditions
- Low Standby Supply Current 1-µA Max
- More Than 100 mV Receiver Hysteresis

APPLICATIONS

- Long Cable Solutions
 - Factory Automation
 - Security Networks
 - Building HVAC
- Severe Electrical Environments
 - Electrical Power Inverters
 - Industrial Drives
 - Avionics



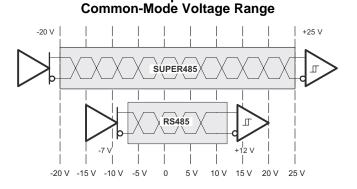
HVD2x APPLICATION SPACE

DESCRIPTION

The transceivers in the HVD2x family offer performance far exceeding typical RS-485 devices. In addition to meeting all requirements of the TIA/EIA-485-A standard, the HVD2x family operates over an extended range of common-mode voltage, and has features such as high ESD protection, wide receiver hysteresis, and failsafe operation. This family of devices is ideally suited for long-cable networks, and other applications where the environment is too harsh for ordinary transceivers.

These devices are designed for bidirectional data transmission on multipoint twisted-pair cables. Example applications are digital motor controllers, remote sensors and terminals, industrial process control, security stations, and environmental control systems.

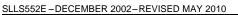
These devices combine a 3-state differential driver and a differential receiver, which operate from a single 5-V power supply. The driver differential outputs and the receiver differential inputs are connected internally to form a differential bus port that offers minimum loading to the bus. This port features an extended common-mode voltage range making the device suitable for multipoint applications over long cable runs.



HVD2x Devices Operate Over a Wider

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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

DESCRIPTION (CONTINUED)

The 'HVD20 provides high signaling rate (up to 25 Mbps) for interconnecting networks of up to 64 nodes.

The 'HVD21 allows up to 256 connected nodes at moderate data rates (up to 5 Mbps). The driver output slew rate is controlled to provide reliable switching with shaped transitions which reduce high-frequency noise emissions.

The 'HVD22 has controlled driver output slew rate for low radiated noise in emission-sensitive applications and for improved signal quality with long stubs. Up to 256 'HVD22 nodes can be connected at signaling rates up to 500 kbps.

The 'HVD23 implements receiver equalization technology for improved jitter performance on differential bus applications with data rates up to 25 Mbps at cable lengths up to 160 meters.

The 'HVD24 implements receiver equalization technology for improved jitter performance on differential bus applications with data rates in the range of 1 Mbps to 10 Mbps at cable lengths up to 1000 meters.

The receivers also include a failsafe circuit that provides a high-level output within 250 microseconds after loss of the input signal. The most common causes of signal loss are disconnected cables, shorted lines, or the absence of any active transmitters on the bus. This feature prevents noise from being received as valid data under these fault conditions. This feature may also be used for Wired-Or bus signaling.

The SN65HVD2X devices are characterized for operation over the temperature range of -40°C to 85°C.

| PART NUMBERS | CABLE LENGTH AND SIGNALING RATE ⁽¹⁾ | NODES | MARKING |
|--------------|---|-----------|-----------------------|
| SN65HVD20 | Up to 50 m at 25 Mbps | Up to 64 | D: VP20 P: 65HVD20 |
| SN65HVD21 | Up to 150 m at 5 Mbps (with slew rate limit) | Up to 256 | D: VP21 P: 65HVD21 |
| SN65HVD22 | Up to1200 m at 500 kbps (with slew rate limit) | Up to 256 | D: VP22 P: 65HVD22 |
| SN65HVD23 | Up to 160 m at 25 Mbps (with receiver equalization) | Up to 64 | D: VP23 P: 65HVD23 |
| SN65HVD24 | Up to 500 m at 3 Mbps (with receiver equalization) | Up to 256 | D: VP24 P: 65HVD24 |

PRODUCT SELECTION GUIDE

(1) Distance and signaling rate predictions based upon Belden 3105A cable and 15% eye pattern jitter.

AVAILABLE OPTIONS

| PLASTIC THROUGH-HOLE | PLASTIC SMALL-OUTLINE ⁽¹⁾ |
|----------------------|--------------------------------------|
| P-PACKAGE | D-PACKAGE |
| (JEDEC MS-001) | (JEDEC MS-012) |
| SN65HVD20P | SN65HVD20D |
| SN65HVD21P | SN65HVD21D |
| SN65HVD22P | SN65HVD22D |
| SN65HVD23P | SN65HVD23D |
| SN65HVD24P | SN65HVD24D |

(1) Add R suffix for taped and reeled carriers.

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| | HVD20, H | IVD21, HVD | 022 | HVD23, HVD24 | | | |
|-------|----------|------------|--------|--------------|--------|----------------|---|
| INPUT | ENABLE | O | JTPUTS | INPUT | ENABLE | ENABLE OUTPUTS | |
| D | DE | Α | В | D | DE | Α | В |
| Н | Н | Н | L | Н | Н | Н | L |
| L | Н | L | Н | L | Н | L | Н |
| Х | L | Z | Z | Х | L | Z | Z |
| Х | OPEN | Z | Z | Х | OPEN | Z | Z |
| OPEN | Н | Н | L | OPEN | н | L | н |

Table 1. DRIVER FUNCTION TABLE

H = high level, L= low level, X = don't care, Z = high impedance (off), ? = indeterminate

| DIFFERENTIAL INPUT V _{ID} = (V _A – V _B) | ENABLE RE | OUTPUT R | | | | |
|--|--------------|------------------------------|--|--|--|--|
| 0.2 V ≤ VID | L | Н | | | | |
| –0.2 V < VID < 0.2 V | L | H (see Note ⁽¹⁾) | | | | |
| VID ≤ -0.2 V | L | L | | | | |
| Х | Н | Z | | | | |
| Х | OPEN | Z | | | | |
| Open circuit | L | Н | | | | |
| Short Circuit | L | Н | | | | |
| Idle (terminated) bus | L | Н | | | | |
| H = high level, L= low level, Z = high impedance (off) | | | | | | |

Table 2. RECEIVER FUNCTION TABLE

 If the differential input V_{ID} remains within the transition range for more than 250 μs, the integrated failsafe circuitry detects a bus fault, and set the receiver output to a high state. See Figure 15.

ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range (unless otherwise noted) ⁽¹⁾

| | | | SN65HVD2X |
|---|--|-----------|----------------------|
| Supply voltage ⁽²⁾ , V _{CC} | | | –0.5 V to 7 V |
| Voltage at any bus I/O terminal | | | –27 V to 27 V |
| Voltage input, transient pulse, A a | and B, (through 100 Ω , see Figur | e 16) | -60 V to 60 V |
| Voltage input at any D, DE or RE | terminal | | -0.5 V to VCC+ 0.5 V |
| Receiver output current, IO | | | -10 mA to 10 mA |
| | Liveran Dark, Madal ⁽³⁾ | A, B, GND | 16 kV |
| Electrostatic | Human Body Model ⁽³⁾ | All pins | 5 kV |
| dischargeElectrostatic discharge | Charged-Device Model ⁽⁴⁾ | All pins | 1.5 kV |
| | Machine Model ⁽⁵⁾ | All pins | 200 V |
| Continuous total power dissipation | า | | See Thermal Table |
| Junction temperature, T _J | | | 150°C |

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltage values, except differential I/O bus voltages, are with respect to network ground terminal.

(3) Tested in accordance with JEDEC Standard 22, Test Method A114-A.

(4) Tested in accordance with JEDEC Standard 22, Test Method C101.

(5) Tested in accordance with JEDEC Standard 22, Test Method A115-A

SN65HVD20, SN65HVD21 SN65HVD22, SN65HVD23, SN65HVD24

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RECOMMENDED OPERATING CONDITIONS

| | | MIN | NOM | MAX | UNIT |
|---|--|------|-----|-----------------|------|
| Supply voltage, V _{CC} | | 4.5 | 5 | 5.5 | V |
| Voltage at any bus I/O terminal | A, B | -20 | | 25 | V |
| High-level input voltage, V _{IH} | | 2 | | V _{CC} | V |
| Low-level input voltage, V _{IL} | input voltage, V _{IL} D, DE, RE | | | 0.8 | V |
| Differential input voltage, V _{ID} | A with respect to B | -25 | | 25 | V |
| | Driver | -110 | | 110 | |
| Output current | Receiver | -8 | | 8 | mA |
| Operating free-air temperature, TA | 1) | -40 | | 85 | °C |
| Junction temperature, T _J | | -40 | | 130 | °C |

(1) Maximum free-air temperature operation is allowed as long as the device recommended junction temperature is not exceeded.

DRIVER ELECTRICAL CHARACTERISTICS

over recommended operating conditions

| PARAMETER | | TEST CONDITIONS | | MIN | TYP ⁽¹) | MAX | UNIT |
|----------------------------|--|--|------------------------|------|------------------------|----------|------|
| V _{IK} | Input clamp voltage | I _I = −18 mA | | -1.5 | 0.75 | | V |
| Vo | Open-circuit output voltage | A or B, No load | | 0 | | V_{CC} | V |
| | | No load (open circuit) | No load (open circuit) | | 4.2 | V_{CC} | |
| V _{OD(SS)} | Steady-state differential output voltage | $R_L = 54 \Omega$, See Figure 1 | | 1.8 | 2.5 | | V |
| | | With common-mode loading, See Figure | 2 | 1.8 | | | |
| $\Delta V_{OD(SS)} $ | Change in steady-state differential output voltage between logic states | See Figure 1 and Figure 3 | | -0.1 | | 0.1 | V |
| V _{OC(SS)} | Steady-state common-mode output voltage | See Figure 1 | | 2.1 | 2.5 | 2.9 | V |
| $\Delta V_{\text{OC(SS)}}$ | Change in steady-state common-mode output voltage, $V_{OC(H)} - V_{OC(L)}$ | See Figure 1 and Figure 4 | | -0.1 | | 0.1 | V |
| V _{OC(PP)} | Peak-to-peak common-mode output voltage, $V_{OC(MAX)} - V_{OC(MIN)}$ | $R_L = 54 \Omega, C_L = 50 \text{ pF}, \text{ See Figure 1 and}$ | d Figure 4 | 0.35 | | | V |
| V _{OD(RING)} | Differential output voltage over and under shoot | $R_L = 54 \ \Omega, \ C_L = 50 \ pF, \ See \ Figure \ 5$ | | | | 10% | |
| l _l | Input current | D, DE | | -100 | | 100 | μA |
| | | | HVD20, HVD23 | -400 | | 500 | |
| | Output current with power off. | $V_0 \le -7$ V to 12 V, Other input = 0 V | HVD21, HVD22, HVD24 | -100 | | 125 | |
| lo | High impedance state output current. | | HVD20, HVD23 | -800 | | 1000 | μA |
| | | $V_0 \le -20$ V to 25 V, Other input = 0 V | HVD21, HVD22, HVD24 | -200 | | 250 | |
| I _{OS} | Short-circuit output current | $V_{O} = -20$ V to 25 V, See Figure 9 | | -250 | | 250 | mA |
| C _{OD} | Differential output capacitance | | | | | 20 | pF |

(1) All typical values are at V_{CC} = 5 V and 25°C.

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Product Folder Link(s): SN65HVD20 SN65HVD21 SN65HVD22 SN65HVD23 SN65HVD24



DRIVER SWITCHING CHARACTERISTICS

over recommended operating conditions

| | PARAMETER | TEST | CONDITIONS | MIN | TYP ⁽¹⁾ | MAX | UNIT |
|-------------------------|--|---|--------------|-----|--------------------|-----|------|
| t _{PLH} | Differential output propagation delay, low-to-high | R_= 54 Ω, | HVD20, HVD23 | 6 | 10 | 20 | |
| | Differential autout proposation delay, high to low | $C_{L} = 50 \text{ pF},$ | HVD21, HVD24 | 20 | 32 | 60 | ns |
| t _{PHL} | Differential output propagation delay, high-to-low | See Figure 3 | HVD22 | 160 | 280 | 500 | |
| t _r | Differential output rise time | R ₁ = 54 Ω, | HVD20, HVD23 | 2 | 6 | 12 | |
| | Differential autout fall time | $C_{L} = 50 \text{ pF},$ | HVD21, HVD24 | 20 | 40 | 60 | ns |
| t _f | Differential output fall time | See Figure 3 | HVD22 | 200 | 400 | 600 | |
| t _{PZH} | Propagation delay time, high-impedance-to-high-level output | | HVD20, HVD23 | | | 40 | |
| | Drepagation delay time, high layel systems to high impedance | RE at 0 V, See Figure 6 HVD21, HVD24 | | | | 100 | ns |
| t _{PHZ} | Propagation delay time, high-level output-to-high-impedance | ecc rigare e | HVD22 | | | 300 | |
| | Dropogotion delouting high impedance to high lovel output | | HVD20, HVD23 | | | 40 | |
| t _{PZL} | Propagation delay time, high-impedance-to-high-level output | RE at 0 V, See Figure 7 HVD21, HVD24 | | | 100 | ns | |
| t _{PLZ} | Propagation delay time, high-level output-to-high-impedance | | HVD22 | | | 300 | |
| t _{d(standby)} | Time from an active differential output to standby | | | | | 2 | μs |
| t _{d(wake)} | Wake-up time from standby to an active differential output | — RE at V _{CC} , See I | Figure o | | | 8 | μs |
| | | HVD20, HVD23 | | | | 2 | |
| t _{sk(p)} | Pulse skew t _{PLH} – t _{PHL} | HVD21, HVD24 | | | | 6 | ns |
| | | HVD22 | | | | 50 | |

(1) All typical values are at $V_{CC} = 5 \text{ V}$ and 25°C

RECEIVER ELECTRICAL CHARACTERISTICS

over recommended operating conditions

| | PARAMETER | TEST | CONDITIONS | MIN | TYP ⁽¹⁾ | MAX | UNIT |
|---------------------|---|---|---|------|--------------------|------|------|
| V _{IT(+)} | Positive-going differential input voltage threshold | 0 | $V_0 = 2.4 \text{ V}, I_0 = -8 \text{ mA}$ | | 60 | 200 | |
| V _{IT(-)} | Negative-going differential input voltage threshold | See Figure 10 | $V_{O} = 0.4 \text{ V}, I_{O} = 8 \text{ mA}$ | -200 | -60 | | mV |
| V _{HYS} | Hysteresis voltage (V _{IT+} – V _{IT-}) | | | 100 | 130 | | mV |
| V | Positive-going differential input failsafe voltage | See Figure 15 | VCM = -7 V to 12 V | 40 | 120 | 200 | mV |
| V _{IT(F+)} | threshold | See Figure 15 | VCM = -20 V to 25 V | | 120 | 250 | mv |
| V | Negative-going differential input failsafe voltage | See Figure 15 | VCM = -7 V to 12 V | -200 | -120 | -40 | mV |
| V _{IT(F-)} | threshold | See Figure 15 | VCM = -20 V to 25 V | -250 | -120 | | mv |
| V _{IK} | Input clamp voltage | I _I = -18 mA | I ₁ = -18 mA | | | | V |
| V _{OH} | High-level output voltage | V _{ID} = 200 mV, I _{OH} : | = −8 mA, See Figure 11 | 4 | | | V |
| V _{OL} | Low-level output voltage | $V_{ID} = -200 \text{ mV}, I_{OL}$ | = 8 mA, See Figure 11 | | | 0.4 | V |
| | | $V_1 = -7$ to 12 V, | HVD20, HVD23 | -400 | | 500 | |
| | | Other input = 0 V | HVD21, HVD22, HVD24 | -100 | | 125 | |
| I _{I(BUS)} | Bus input current (power on or power off) | $V_1 = -20$ to 25 V, | HVD20, HVD23 | -800 | | 1000 | μA |
| | | Other input = 0 V | HVD21, HVD22, HVD24 | -200 | | 250 | |
| I _I | Input current | RE | RE | | | 100 | μA |
| (| | HVD20, HVD23 | | 24 | | | 1.0 |
| RI | Input resistanceInput resistance | HVD21, HVD22, H | HVD21, HVD22, HVD24 | | | | kΩ |
| CID | Differential input capacitance | V _{ID} = 0.5 + 0.4 sine | e (2π × 1.5 × 10 ⁶ t) | | 20 | | pF |

(1) All typical values are at 25°C.

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EXAS

RECEIVER SWITCHING CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

| | PARAMETER | TEST | CONDITIONS | MIN | ТҮР | MAX | UNIT |
|-------------------------|--|-----------------------------------|------------------------|-----|-----|-----|------|
| t _{PLH} | Propagation delay time, low-to-high level output | | HVD20, HVD23 | | 16 | 35 | ns |
| t _{PHL} | Propagation delay time high-to low level output | See Figure 11 | HVD21, HVD22, HVD24 | | 25 | 50 | |
| tr t _f | Receiver output rise time Receiver output fall time | See Figure 11 | | | 2 | 4 | ns |
| t _{PZH} | Receiver output enable time to high level | See Figure 12 | | | 90 | 120 | ns |
| t _{PHZ} | Receiver output disable time from high level | | | | 16 | 35 | |
| t _{PZL} | Receiver output enable time to low level | | | | 90 | 120 | ns |
| t _{PLZ} | Receiver output disable time from low level | See Figure 13 | | | 16 | 35 | |
| t _{r(standby)} | Time from an active receiver output to standby | 0 | | | | 2 | μs |
| t _{r(wake)} | Wake-up time from standby to an active receiver output | See Figure 14, DE at 0 V | | | | 8 | |
| t _{sk(p)} | Pulse skew t _{PLH} – t _{PHL} | | | | | 5 | |
| t _{p(set)} | Delay time, bus fail to failsafe set | See Figure 15, pulse rate = 1 kHz | | | 250 | 350 | μs |
| t _{p(reset)} | Delay time, bus recovery to failsafe reset | | | | 50 | | ns |

RECEIVER EQUALIZATION CHARACTERISTICS⁽¹⁾

over recommended operating conditions

| P | ARAMETER | TEST CO | NDITIONS | | | MIN TYP ⁽²⁾ | MAX | UNIT | | | | |
|------|--|----------------------------------|----------------|---|---------------|------------------------|--------|-------|-------|-----|--|----|
| | | | | 0 m | HVD23 | 2 | | ns | | | | |
| | | | | 100 m | HVD20 | 6 | | ~~~ | | | | |
| | | | | 100 m | HVD23 | 3 | | ns | | | | |
| | | | 25 Mbps | 150 m | HVD20 | 15 | | ns | | | | |
| | | | | 150 11 | HVD23 | 4 | | 115 | | | | |
| | | | | 200 m | HVD20 | 27 | | ns | | | | |
| | | | | 200 111 | HVD23 | 8 | | 115 | | | | |
| | | | | 200 m | HVD20 | 22 | | ns | | | | |
| | | | | 200 111 | HVD23 | 8 | | 113 | | | | |
| | Dealsternels | Peudo-random NRZ code with a bit | | 250 m | HVD20 | 34 | | ns | | | | |
| (pp) | Peak-to-peak eye-pattern jitterpattern length of 216 – 1, Beldon 3105A cable, See Figure 27 | 3105A cable, | r 3105A cable, | tern jitter 3105A cable, See Figure 27 | 230 111 | HVD23 | 15 | | 115 | | | |
| | | | | | See Figure 27 | See Figure 27 | | 300 m | HVD20 | 49 | | ns |
| | | | | 500 11 | HVD23 | 27 | | 115 | | | | |
| | | | | | | | 5 Mbps | 500 m | HVD21 | 128 | | ns |
| | | | | 500 11 | HVD24 | 18 | | 115 | | | | |
| | | | | | HVD20 | 93 | | | | | | |
| | | | 3 Mbpc | 500 m | HVD21 | 103 | | 00 | | | | |
| | | | 3 Mbps | 500 m | HVD23 | 90 | | ns | | | | |
| | | | | | HVD24 | 16 | | | | | | |
| | | | 1 Mbps | 1000 m | HVD21 | 216 | | ne | | | | |
| | | | r wups | 1000 m | HVD24 | 62 | | ns | | | | |

The HVD20 and HVD21 do not have receiver equalization, but are specified for comparison. All typical values are at V_{CC} = 5 V, and temperature = 25°C. (1)

(2)

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Product Folder Link(s): SN65HVD20 SN65HVD21 SN65HVD22 SN65HVD23 SN65HVD24



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SUPPLY CURRENT

over recommended operating conditions (unless otherwise noted)

| Ρ | ARAMETER | TEST CONDITIONS | | MIN | ТҮР | MAX | UNIT |
|-----|--------------------------|---|-----------|-----|-----|-----|------|
| | | | HVD20 | | 6 | 9 | |
| | | | HVD21 | | 8 | 12 | |
| | | | HVD22 | | 6 | 9 | |
| | | Driver enabled (DE at V _{CC}), Receiver enabled (RE at 0 V), No load, $V_I = 0$ V or V _{CC} | HVD23 | | 7 | 11 | mA |
| | | | HVD24 | | 10 | 14 | |
| | | | HVD20 | | 5 | 8 | |
| | | | HVD21 | | 7 | 11 | |
| | Supply | | HVD22 | | 5 | 8 | |
| ICC | current | Driver enabled (DE at V_{CC}), Receiver disabled (RE at V_{CC}), No load, $V_I = 0 V$ or V_{CC} | HVD23 | | 5 | 9 | mA |
| | | | HVD24 | | 8 | 12 | |
| | | | HVD20 | | 4 | 7 | |
| | | | HVD21 | | 5 | 8 | |
| | Driver disabled (DE at 0 | Driver disabled (DE at 0 V), Receiver enabled (RE at 0 V), No load | HVD22 | | 4 | 7 | mA |
| | | | HVD23 | | 4.5 | 9 | |
| | | | HVD24 | | 5.5 | 10 | |
| | | Driver disabled (DE at 0 V), Receiver disabled (RE at V_{CC}) D open | All HVD2x | | | 1 | μA |

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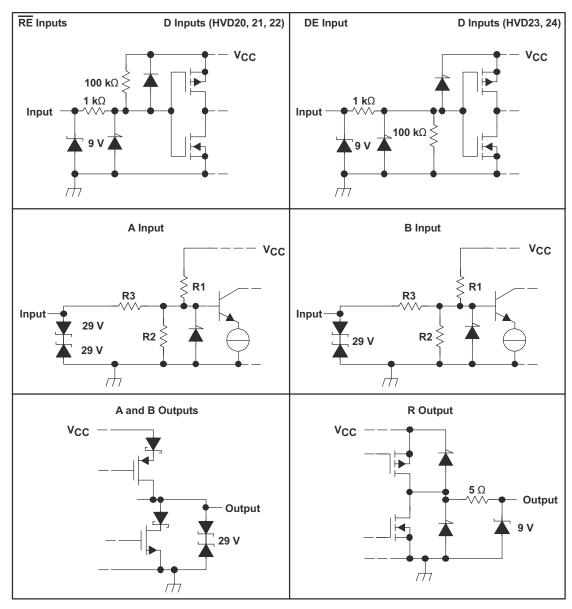
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INSTRUMENTS

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EQUIVALENT INPUT AND OUTPUT SCHEMATIC DIAGRAMS



| | R1/R2 | R3 |
|---------------|-------|--------|
| HVD20, 23 | 9 kΩ | 45 kΩ |
| HVD21, 22, 24 | 36 kΩ | 180 kΩ |

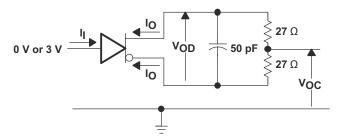


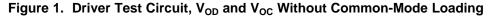
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PARAMETER MEASUREMENT INFORMATION

NOTE: Test load capacitance includes probe and jig capacitance (unless otherwise specified). Signal generator characteristics: rise and fall time <6 ns, pulse rate 100 kHz, 50% duty cycle, Zo = 50 Ω (unless otherwise specified).





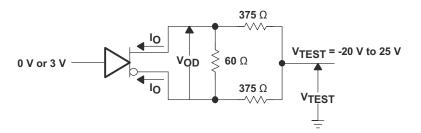


Figure 2. Driver Test Circuit, V_{OD} With Common-Mode Loading

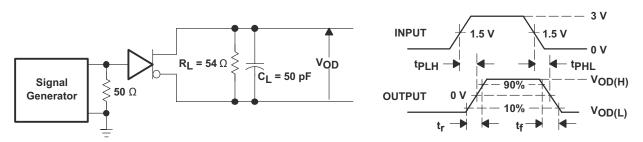


Figure 3. Driver Switching Test Circuit and Waveforms

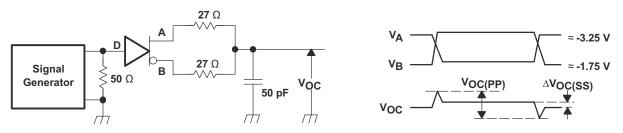
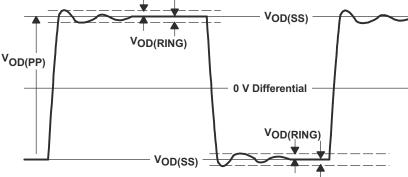


Figure 4. Driver V_{OC} Test Circuit and Waveforms

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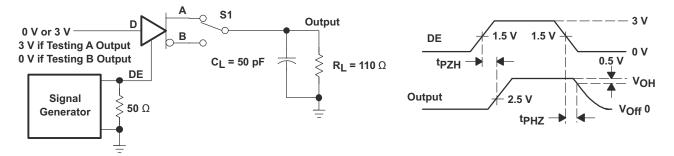




PARAMETER MEASUREMENT INFORMATION (continued)

NOTE: $V_{OD(RING)}$ is measured at four points on the output waveform, corresponding to overshoot and undershoot from the $V_{OD(H)}$ and $V_{OD(L)}$ steady state values.







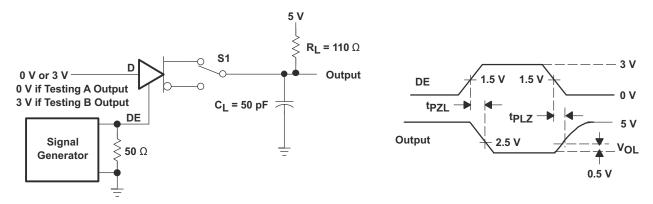


Figure 7. Driver Enable/Disable Test, Low Output

NSTRUMENTS

EXAS

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PARAMETER MEASUREMENT INFORMATION (continued)

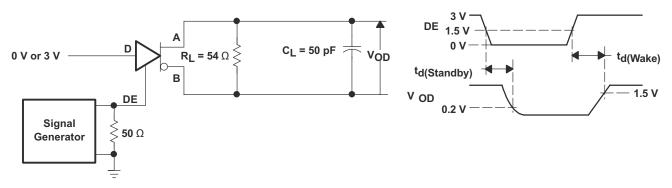


Figure 8. Driver Standby/Wake Test Circuit and Waveforms

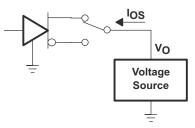


Figure 9. Driver Short-Circuit Test

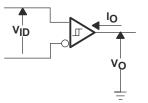


Figure 10. Receiver DC Parameter Definitions

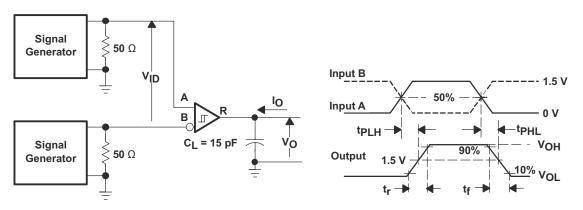


Figure 11. Receiver Switching Test Circuit and Waveforms

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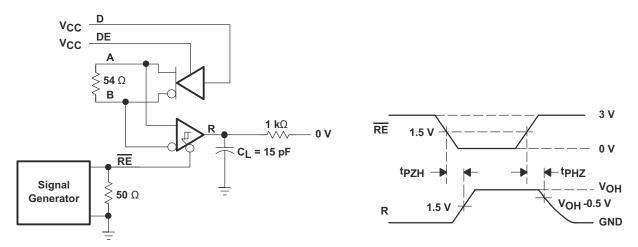


Figure 12. Receiver Enable Test Circuit and Waveforms, Data Output High

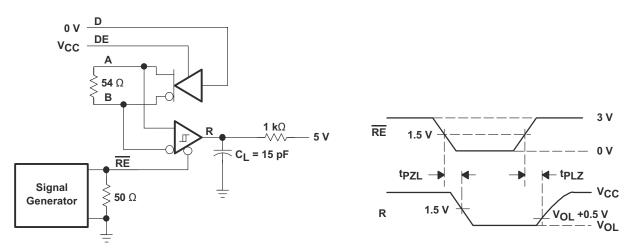


Figure 13. Receiver Enable Test Circuit and Waveforms, Data Output Low

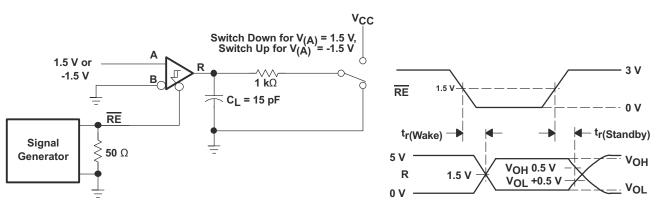


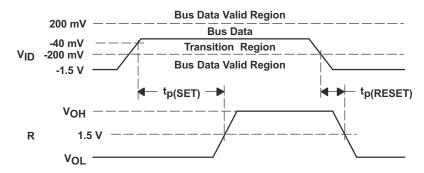
Figure 14. Receiver Standby and Wake Test Circuit and Waveforms

Product Folder Link(s): SN65HVD20 SN65HVD21 SN65HVD22 SN65HVD23 SN65HVD24



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PARAMETER MEASUREMENT INFORMATION (continued)





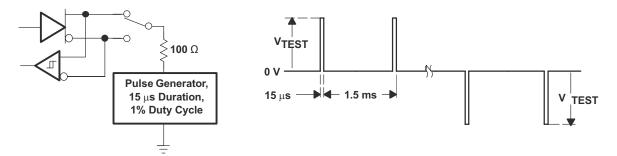
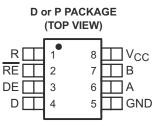
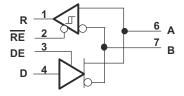


Figure 16. Test Circuit and Waveforms, Transient Overvoltage Test

PIN ASSIGNMENTS



LOGIC DIAGRAM



SN65HVD20, SN65HVD21 SN65HVD22, SN65HVD23, SN65HVD24

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THERMAL INFORMATION

| | | SN65H | SN65HVD2x | | | | |
|-----------------------|---|----------|-----------|-------|--|--|--|
| | THERMAL METRIC ⁽¹⁾ | SOIC (D) | PDIP (P) | UNITS | | | |
| | | 8 PINS | PINS | | | | |
| θ _{JA} | Junction-to-ambient thermal resistance ⁽²⁾ | 78.1 | 52.5 | | | | |
| θ _{JC(top)} | Junction-to-case(top) thermal resistance (3) | 56.5 | 57.6 | | | | |
| θ _{JB} | Junction-to-board thermal resistance (4) | 50.4 | 38.6 | *CAA/ | | | |
| ΨJT | Junction-to-top characterization parameter ⁽⁵⁾ | 4.1 | 19.1 | °C/W | | | |
| Ψ _{JB} | Junction-to-board characterization parameter (6) | 32.6 | 31.9 | | | | |
| $\theta_{JC(bottom)}$ | Junction-to-case(bottom) thermal resistance (7) | nA | n/A | | | | |

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, SPRA953.
 (2) The junction-to-ambient thermal resistance under natural convection is obtained in a simulation on a JEDEC-standard, high-K board, as

specified in JESD51-7, in an environment described in JESD51-2a.

(3) The junction-to-case (top) thermal resistance is obtained by simulating a cold plate test on the package top. No specific JEDEC-standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.

(4) The junction-to-board thermal resistance is obtained by simulating in an environment with a ring cold plate fixture to control the PCB temperature, as described in JESD51-8.

(5) The junction-to-top characterization parameter, ψ_{JT} , estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining θ_{JA} , using a procedure described in JESD51-2a (sections 6 and 7).

(6) The junction-to-board characterization parameter, ψ_{JB} , estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining θ_{JA} , using a procedure described in JESD51-2a (sections 6 and 7).

(7) The junction-to-case (bottom) thermal resistance is obtained by simulating a cold plate test on the exposed (power) pad. No specific JEDEC standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.

POWER DISSIPATION

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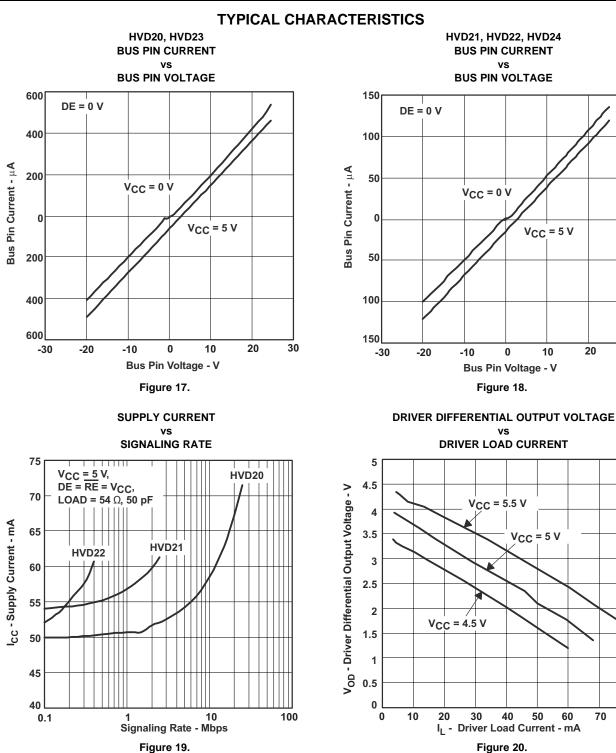
| PA | ARAMETERS | | TEST CONDITIONS | | VALUE | UNIT |
|---|------------|-------|---|----------|-------|------|
| Device Power | | HVD20 | $V_{CC} = 5 \text{ V}, \text{ T}_{J} = 25^{\circ}\text{C},$ | 25 Mbps | 295 | |
| | | HVD21 | $R_L = 54 \Omega$, $C_L = 50 pF$ (driver), $C_L = 15 pF$ (receiver), | 5 Mbps | 260 | |
| | Typical | HVD22 | 50% Duty cycle square-wave signal, | 500 kbps | 233 | mW |
| | | HVD23 | Driver and receiver enabled | 25 Mbps | 302 | |
| | | HVD24 | | 5 Mbps | 267 | |
| dissipation, P _D | | HVD20 | $V_{CC} = 5.5 \text{ V}, \text{ T}_{J} = 125^{\circ}\text{C},$ | 25 Mbps | 408 | |
| | | HVD21 | $R_L = 54 \Omega, C_L = 50 pF,$ $C_L = 15 pF (receiver),$ 50% Duty cycle square-wave signal, Driver and receiver enabled | 5 Mbps | 342 | |
| | Worst case | HVD22 | | 500 kbps | 300 | mW |
| | | HVD23 | | 25 Mbps | 417 | |
| | | HVD24 | | 5 Mbps | 352 | |
| Thermal shut down junction temperature, T _{SD} | | | | | 170 | °C |



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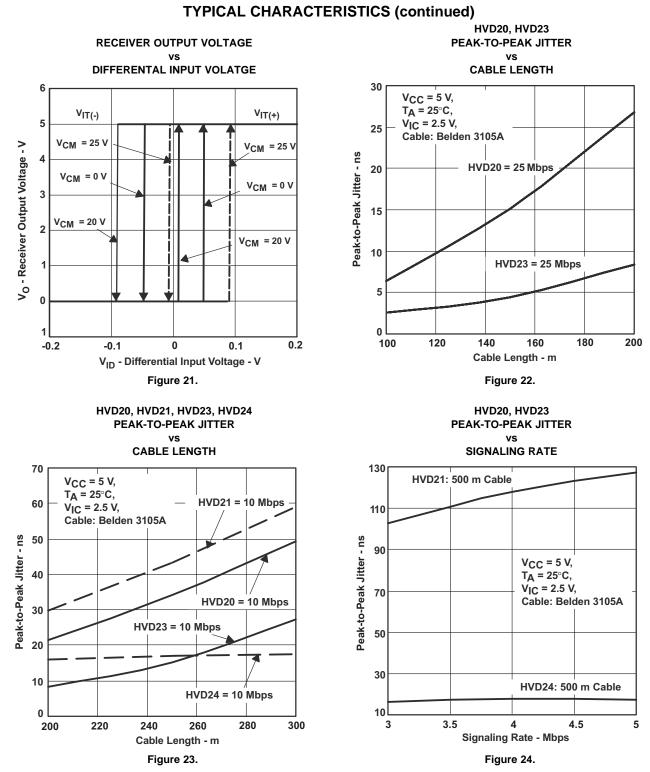
30

80



Product Folder Link(s): SN65HVD20 SN65HVD21 SN65HVD22 SN65HVD23 SN65HVD24





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2010



APPLICATION INFORMATION

THEORY OF OPERATION

The HVD2x family of devices integrates a differential receiver and differential driver with additional features for improved performance in electrically-noisy, long-cable, or other fault-intolerant applications.

The receiver hysteresis (typically 130 mV) is much larger than found in typical RS-485 transceivers. This helps reject spurious noise signals which would otherwise cause false changes in the receiver output state.

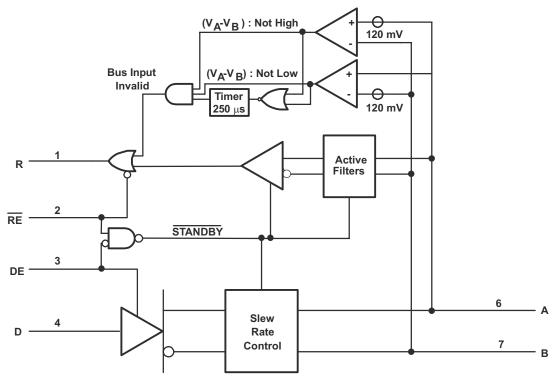
Slew rate limiting on the driver outputs (SN65HVD21, 22, and 24) reduces the high-frequency content of signal edges. This decreases reflections from bus discontinuities, and allows longer stub lengths between nodes and the main bus line. Designers should consider the maximum signaling rate and cable length required for a specific application, and choose the transceiver best matching those requirements.

When DE is low, the differential driver is disabled, and the A and B outputs are in high-impedance states. When DE is high, the differential driver is enabled, and drives the A and B outputs according to the state of the D input.s

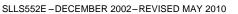
When \overline{RE} is high, the differential receiver output buffer is disabled, and the R output is in a high-impedance state. When \overline{RE} is low, the differential receiver is enabled, and the R output reflects the state of the differential bus inputs on the A and B pins.

If both the driver and receiver are disabled, (DE low and \overline{RE} high) then all nonessential circuitry, including auxiliary functions such as failsafe and receiver equalization is placed in a low-power standby state. This reduces power consumption to less than 5µW. When either enable input is asserted, the circuitry again becomes active.

In addition to the primary differential receiver, these devices incorporate a set of comparators and logic to implement an active receiver failsafe feature. These components determine whether the differential bus signal is valid. Whenever the differential signal is close to zero volts (neither high nor low), a timer initiates, If the differential input remains within the transition range for more than 250 microseconds, the timer expires and set the receiver output to the high state. If a valid bus input (high or low) is received at any time, the receiver output reflects the valid bus state, and the timer is reset.







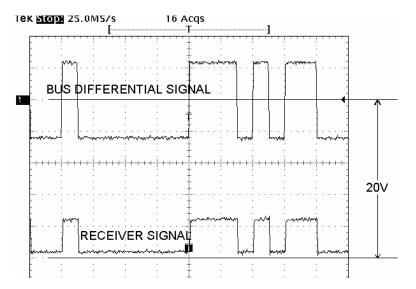


Figure 26. HVD22 Receiver Operation With 20-V Offset on Input Signal

| $H(s) = k_0 \left[(1-k_1) + \frac{k_1 p_1}{(s+p_1)} \right] \left[(1-k_2) + \frac{k_2 p_2}{(s+p_2)} \right] \left[(1-k_3) + \frac{k_3 p_3}{(s+p_3)} \right]$ | k0 (DC loss) | p1 (MHz) | k1 | p2 (MHz) | k2 | p3 (MHz) | k3 |
|---|--------------------|-------------|-----|-------------|-----|-------------|----|
| Similar to 160m of Belden 3105A | 0.95 | 0.25 | 0.3 | 3.5 | 0.5 | 15 | 1 |
| Similar to 250m of Belden 3105A | 0.9 | 0.25 | 0.4 | 3.5 | 0.7 | 12 | 1 |
| Similar to 500m of Belden 3105A | 0.8 | 0.25 | 0.6 | 2.2 | 1 | 8 | 1 |
| Similar to 1000m of Belden 3105A | 0.6 | 0.3 | 1 | 3 | 1 | 6 | 1 |



Figure 27. Cable Attenuation Model for Jitter Measurements





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INTEGRATED RECEIVER EQUALIZATION USING THE HVD23

Figure 28 illustrates the benefits of integrated receiver equalization as implemented in the HVD23 transceiver. In this test setup, a differential signal generator applied a signal voltage at one end of the cable, which was Belden 3105A twisted-pair shielded cable. The test signal was a pseudo-random bit stream (PRBS) of nonreturn-to-zero (NRZ) data. Channel 1 (top) shows the eye-pattern of the differential voltage at the receiver inputs (after the cable attenuation). Channel 2 (bottom) shows the output of the receiver.

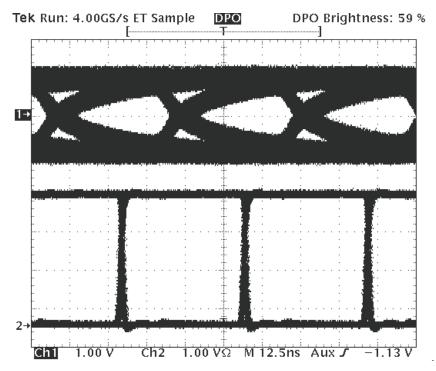


Figure 28. HVD23 Receiver Performance at 25 Mbps Over 150 Meter Cable

SN65HVD20, SN65HVD21 SN65HVD22, SN65HVD23, SN65HVD24

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INTEGRATED RECEIVER EQUALIZATION USING THE HVD24

Figure 29 illustrates the benefits of integrated receiver equalization as implemented in the HVD24 transceiver. In this test setup, a differential signal generator applied a signal voltage at one end of the cable, which was Belden 3105A twisted-pair shielded cable. The test signal was a pseudo-random bit stream (PRBS) of nonreturn-to-zero (NRZ) data. Channel 1 (top) shows the eye-pattern of the bit stream. Channel 2 (middle) shows the eye-pattern of the differential voltage at the receiver inputs (after the cable attenuation). Channel 3 (bottom) shows the output of the receiver.

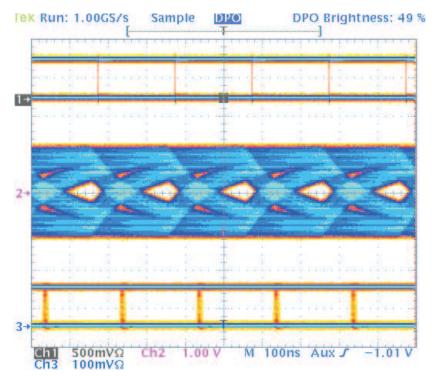


Figure 29. HVD24 Receiver Performance at 5 Mbps Over 500 Meter Cable



NOISE CONSIDERATIONS FOR EQUALIZED RECEIVERS

The simplest way of overcoming the effects of cable losses is to increase the sensitivity of the receiver. If the maximum attenuation of frequencies of interest is 20 dB, increasing the receiver gain by a factor of ten compensates for the cable. However, this means that both signal and noise are amplified. Therefore, the receiver with higher gain is more sensitive to noise and it is important to minimize differential noise coupling to the equalized receiver.

Differential noise is crated when conducted or radiated noise energy generates more voltage on one line of the differential pair than the other. For this to occur from conducted or electric far-field noise, the impedance to ground of the lines must differ.

For noise frequency out to 50 MHz, the input traces can be treated as a lumped capacitance if the receiver is approximately 10 inches or less from the connector. Therefore, matching impedance of the lines is accomplished by matching the lumped capacitance of each.

The primary factors that affect the capacitance of a trace are in length, thickness, width, dielectric material, distance from the signal return path, stray capacitance, and proximity to other conductors. It is difficult to match each of the variables for each line of the differential pair exactly, but a reasonable effort to do so keeps the lines balanced and less susceptible to differential noise coupling.

Another source of differential noise is from near-field coupling. In this situation, an assumption of equal noise-source impedance cannot be made as in the far-field. Familiarly known as crosstalk, more energy from a nearby signal is coupled to one line of the differential pair. Minimization of this differential noise is accomplished by keeping the signal pair close together and physical separation from high-voltage, high-current, or high-frequency signals.

In summary, follow these guidelines in board layout for keeping differential noise to a minimum.

- · Keep the differential input traces short.
- Match the length, physical dimensions, and routing of each line of the pair.
- Keep the lines close together.
- Match components connected to each line.
- Separate the inputs from high-voltage, high-frequency, or high-current signals.

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TEST MODE DRIVER DISABLE

If the input signal to the D pin is such that:

- 1. the signal has signaling rate above 4 Mbps (for the 'HVD21 and 'HVD24)
- 2. the signal has signaling rate above 6 Mbps (for the 'HVD20 and 'HVD23)
- 3. the signal has average amplitude between 1.2 V and 1.6 V (1.4 V ±200 mV)
- 4. the average signal amplitude remains in this range for 100 µsec or longer,

then the driver may activate a test-mode during which the driver outputs are temporarily disabled. This can cause loss of transmission of data during the period that the device is in the test-mode. The driver will be re-enabled and resume normal operation whenever the above conditions are not true. The device is not damaged by this test mode.

Although rare, there are combinations of specific voltage levels and input data patterns within the operating conditions of the HVD2x family which may lead to a temporary state where the driver outputs are disabled for a period of time.

Observations:

- 1. The conditions for inadvertently entering the test mode are dependent on the levels, duration, and duty cycle of the logic signal input to the D pin. Operating input levels are specified as greater than 2 V for a logic HIGH input, and less than 0.8V for a logic LOW input. Therefore, a valid steady-state logic input will not cause the device to activate the test mode
- 2. Only input signals with frequency content above 2 MHz (4 Mbps) have a possibility of activating the test mode. Therefore, this issue should not affect the normal operation of the HVD22 (500 kbps).
- 3. For operating signaling rates of 4 Mbps (or above), the conditions stated above must remain true over a period of: 4 Mbps x 100 µsec = 400 bits. Therefore, a normal short message will not inadvertently activate the test model
- 4. One example of an input signal which may cause the test mode to activate is a clock signal with frequency 3 MHz and 50% duty cycle (symmetric HIGH and LOW half-cycles) with logic HIGH levels of 2.4 V and logic LOW levels of 0.4 V. This signal applied to the D pin as a driver input would meet the criteria listed above, and might cause the test-mode to activate, which would disable the driver. Note that this example situation might occur if the clock signal were generated by a microcontroller or logic chip with a 2.7 V-supply.

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SN65HVD20, SN65HVD21 SN65HVD22, SN65HVD23, SN65HVD24

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REVISION HISTORY

Changes from Original (December 2002) to Revision A Page Changed t_{PZH}, t_{PHZ}, t_{PZL}, and t_{PLZ} - From a MAX value of 120 To include TYP and MAX values for each entry Changes from Revision A (March 2003) to Revision B Page Changes from Revision B (June 2003) to Revision C Page Added the NOISE CONSIDERATIONS FOR EQUALIZED RECEIVERS section Changes from Revision C (September 2003) to Revision D Page Added Conditions note to the ABSOLUTE MAXIMUM RATINGS table "over operating free-air temperature range Changes from Revision D (April 2005) to Revision E Page

| | table) | . 4 |
|---|--|-----|
| | Replaced the Dissipation Rating table with the THERMAL INFORMATION table | |
| • | Changed the THERMAL CHARACTERISTICS table to POWER DISSIPATION table | 14 |
| • | Added the TEST MODE DRIVER DISABLE section | 22 |





24-Apr-2015

PACKAGING INFORMATION

| Orderable Device | | Package Type | Package Drawing | Pins | • | | Lead/Ball Finish | MSL Peak Temp | Op Temp (°C) | Device Marking | Samples |
|------------------|--------|--------------|--------------------|------|------|----------------------------|------------------|--------------------|--------------|----------------|---------|
| | (1) | | | | Qty | (2) | (6) | (3) | | (4/5) | |
| SN65HVD20D | ACTIVE | SOIC | D | 8 | 75 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | -40 to 85 | VP20 | Samples |
| SN65HVD20DG4 | ACTIVE | SOIC | D | 8 | 75 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | -40 to 85 | VP20 | Samples |
| SN65HVD20DR | ACTIVE | SOIC | D | 8 | 2500 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | -40 to 85 | VP20 | Samples |
| SN65HVD20DRG4 | ACTIVE | SOIC | D | 8 | | TBD | Call TI | Call TI | -40 to 85 | | Samples |
| SN65HVD20P | ACTIVE | PDIP | Ρ | 8 | 50 | Pb-Free (RoHS) | CU NIPDAU | N / A for Pkg Type | -40 to 85 | 65HVD20 | Samples |
| SN65HVD21D | ACTIVE | SOIC | D | 8 | 75 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | -40 to 85 | VP21 | Samples |
| SN65HVD21DG4 | ACTIVE | SOIC | D | 8 | 75 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | -40 to 85 | VP21 | Samples |
| SN65HVD21DR | ACTIVE | SOIC | D | 8 | 2500 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | -40 to 85 | VP21 | Samples |
| SN65HVD21DRG4 | ACTIVE | SOIC | D | 8 | 2500 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | -40 to 85 | VP21 | Samples |
| SN65HVD21P | ACTIVE | PDIP | Р | 8 | 50 | Pb-Free (RoHS) | CU NIPDAU | N / A for Pkg Type | -40 to 85 | 65HVD21 | Samples |
| SN65HVD21PE4 | ACTIVE | PDIP | Ρ | 8 | 50 | Pb-Free (RoHS) | CU NIPDAU | N / A for Pkg Type | -40 to 85 | 65HVD21 | Samples |
| SN65HVD22D | ACTIVE | SOIC | D | 8 | 75 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | -40 to 85 | VP22 | Samples |
| SN65HVD22DG4 | ACTIVE | SOIC | D | 8 | 75 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | -40 to 85 | VP22 | Samples |
| SN65HVD22DR | ACTIVE | SOIC | D | 8 | 2500 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | -40 to 85 | VP22 | Samples |
| SN65HVD22DRG4 | ACTIVE | SOIC | D | 8 | 2500 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | -40 to 85 | VP22 | Samples |
| SN65HVD22P | ACTIVE | PDIP | Р | 8 | 50 | Pb-Free (RoHS) | CU NIPDAU | N / A for Pkg Type | -40 to 85 | 65HVD22 | Samples |
| SN65HVD22PE4 | ACTIVE | PDIP | Р | 8 | 50 | Pb-Free (RoHS) | CU NIPDAU | N / A for Pkg Type | -40 to 85 | 65HVD22 | Samples |



PACKAGE OPTION ADDENDUM

24-Apr-2015

| Orderable Device | Status | Package Type | Package Drawing | Pins | Package Qty | Eco Plan (2) | Lead/Ball Finish (6) | MSL Peak Temp | Op Temp (°C) | Device Marking (4/5) | Samples |
|------------------|--------|--------------|--------------------|------|----------------|----------------------------|-------------------------|--------------------|--------------|-------------------------|---------|
| SN65HVD23D | ACTIVE | SOIC | D | 8 | 75 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | -40 to 85 | VP23 | Samples |
| SN65HVD23DG4 | ACTIVE | SOIC | D | 8 | 75 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | -40 to 85 | VP23 | Samples |
| SN65HVD23DR | ACTIVE | SOIC | D | 8 | 2500 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | -40 to 85 | VP23 | Samples |
| SN65HVD23DRG4 | ACTIVE | SOIC | D | 8 | 2500 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | -40 to 85 | VP23 | Samples |
| SN65HVD23P | ACTIVE | PDIP | Р | 8 | 50 | Pb-Free (RoHS) | CU NIPDAU | N / A for Pkg Type | -40 to 85 | 65HVD23 | Samples |
| SN65HVD24D | ACTIVE | SOIC | D | 8 | 75 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | -40 to 85 | VP24 | Samples |
| SN65HVD24DG4 | ACTIVE | SOIC | D | 8 | 75 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | -40 to 85 | VP24 | Samples |
| SN65HVD24DR | ACTIVE | SOIC | D | 8 | 2500 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | -40 to 85 | VP24 | Samples |
| SN65HVD24DRG4 | ACTIVE | SOIC | D | 8 | 2500 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | -40 to 85 | VP24 | Samples |
| SN65HVD24P | ACTIVE | PDIP | Р | 8 | 50 | Pb-Free (RoHS) | CU NIPDAU | N / A for Pkg Type | -40 to 85 | 65HVD24 | Samples |

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)



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⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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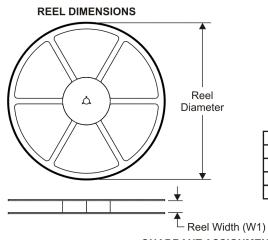
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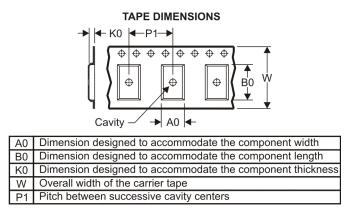
PACKAGE MATERIALS INFORMATION

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Texas Instruments

TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



| Device | Package Type | Package Drawing | | SPQ | Reel Diameter (mm) | Reel Width W1 (mm) | A0 (mm) | B0 (mm) | K0 (mm) | P1 (mm) | W (mm) | Pin1 Quadrant |
|-------------|-----------------|--------------------|---|------|--------------------------|--------------------------|------------|------------|------------|------------|-----------|------------------|
| SN65HVD20DR | SOIC | D | 8 | 2500 | 330.0 | 12.4 | 6.4 | 5.2 | 2.1 | 8.0 | 12.0 | Q1 |
| SN65HVD21DR | SOIC | D | 8 | 2500 | 330.0 | 12.4 | 6.4 | 5.2 | 2.1 | 8.0 | 12.0 | Q1 |
| SN65HVD22DR | SOIC | D | 8 | 2500 | 330.0 | 12.4 | 6.4 | 5.2 | 2.1 | 8.0 | 12.0 | Q1 |
| SN65HVD23DR | SOIC | D | 8 | 2500 | 330.0 | 12.4 | 6.4 | 5.2 | 2.1 | 8.0 | 12.0 | Q1 |
| SN65HVD24DR | SOIC | D | 8 | 2500 | 330.0 | 12.4 | 6.4 | 5.2 | 2.1 | 8.0 | 12.0 | Q1 |

TEXAS INSTRUMENTS

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PACKAGE MATERIALS INFORMATION

4-May-2010



*All dimensions are nominal

| Device | Package Type | Package Drawing | Pins | SPQ | Length (mm) | Width (mm) | Height (mm) |
|-------------|--------------|-----------------|------|------|-------------|------------|-------------|
| SN65HVD20DR | SOIC | D | 8 | 2500 | 340.5 | 338.1 | 20.6 |
| SN65HVD21DR | SOIC | D | 8 | 2500 | 340.5 | 338.1 | 20.6 |
| SN65HVD22DR | SOIC | D | 8 | 2500 | 340.5 | 338.1 | 20.6 |
| SN65HVD23DR | SOIC | D | 8 | 2500 | 340.5 | 338.1 | 20.6 |
| SN65HVD24DR | SOIC | D | 8 | 2500 | 340.5 | 338.1 | 20.6 |

P(R-PDIP-T8)

PLASTIC DUAL-IN-LINE PACKAGE



- A. All linear dimensions are in inches (millimeters).B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-001 variation BA.



D (R-PDSO-G8)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AA.





NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
 E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



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